

YZPST-BT151 SCR_S

●Main Feature (T_j=25℃)

Symbol	Value	Unit
I _{T(AV)}	7.5	A
V _{DRM} / V _{RRM}	≥ 600	V
I _{GT}	1 to 20	mA

●Absolute ratings (Limiting Values)

Symbol	Parameter	Value	Unit
I _{T(RMS)}	RMS on-state current (180° conduction angle)	12	A
I _{T(AV)}	AV on-state current (180° conduction angle)	7.5	A
I _{TSM}	Non repetitive surge peak on-state Current (tp=10ms)	100	A
I ² t	(tp=10ms)	50	A ² S
I _{GM}	Peak gate current(tp=20us)	2	A
P _{GM}	Peak gate power	5	W
P _{G(AV)}	Average gate power	0.5	W
T _{stg}	Storage temperature	-40--+150	℃
T _j	Operating junction temperature	-40--+125	

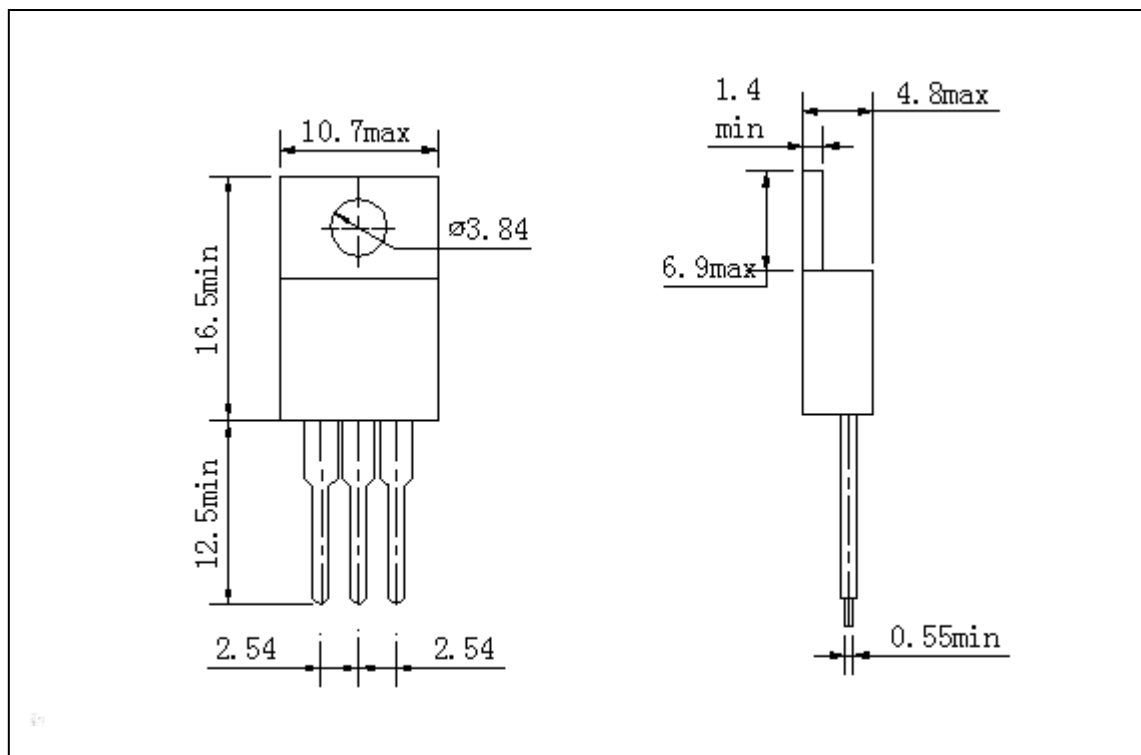
●Thermai Resistances

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case	1.3	K/W
R _{th(j-a)}	Junction to ambient	60	K/W

●Electrical characteristics (T_j=25℃ unless otherwise stated)

Symbol	Test Conditions	Value			Unit
		Min	Type	Max	
I _{GT}	V _D =6V, R _L =100 Ω	1	5	20	uA
V _{GT}	V _D =12V, R _L =100 Ω	-----	0.7	0.8	V
V _{GD}	V _D =V _{DRM} , R _L =3.3K Ω T _j =110℃	0.2	-----	-----	V
I _H	I _r =100mA Gate Open	-----	9	20	mA
dV/dt	V _D =67%V _{DRM} , GateOpen, T _j =125℃	50	125	-----	v/ μ s
V _{TM}	I _r =16A, t _p =380 μ s	-----	-----	1.7	V
I _{DRM}	V _D =V _{DRM} T _j =25℃	-----	-----	20	uA
I _{RRM}	V _R =V _{RRM} T _j =110℃	-----	-----	300	uA

●Measure of package (TO-220E)



●Electrocircuit:

